Abstracts

V-Band InP Gunn Diode

D. Yanmao, Z. Hongzhi, S. Youngxi and F. Jingzhi. "V-Band InP Gunn Diode." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 516-516.

The n/sup +/-n-n/sup +/ InP wafers are continually grown by VPE. An integral heat sink process is utilized to fabricate CW InP Gunn diodes with multiple-layer n/sup +/-n-n/sup +/, which operate in V-band. The rf performance of the diode is determined using a coaxial waveguide cavity. CW output powers of 151 mW at 50.6 GHz and 147 mW at 58.3 GHz have been achieved with efficiencies of 2.48% and 2. 54%, respectively.

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